

ANIRUDHA BEHERA

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SUMMARY

Passionate **Physical Design Engineer** with over **2 years of experience** in end-to-end **ASIC design flow**, specializing in **Place-and-Route (PnR)**, **Static Timing Analysis (STA)**, and **low-power design methodologies**. Skilled in **RTL-to-GDSII implementation**, design optimization, and **PPA improvement** across advanced technology nodes. Proficient in industry-standard **Synopsys and Cadence** toolchains with strong debugging, floorplanning, and timing closure expertise.

SKILLS

Programming Languages: Perl, TCL, Bash, Python (basics), Verilog HDL, Makefile

EDA Tools: Synopsys Design Compiler, ICC2, PrimeTime, StarRC, IC Validator, Cadence Virtuoso, Encounter, Calibre

Physical Design Processes: Logic Synthesis, Floorplan, Power Planning, Placement, Routing, CTS, STA, DRC/LVS, ECO, UPF/CPF, RC Extraction, DFT, SDC/Timing Constraints

EXPERIENCE

Honorex Technologies, Washington, USA

May 2024 – Present

Physical Design Engineer for Marvell Semiconductor

- Executed Place and Route (PnR) for a 7nm AI accelerator block with ~2M standard cells and 32 macros, achieving stringent PPA targets under multi-corner, multi-mode (MCMC) analysis.
- Designed for 2.2 GHz using a multi-VDD architecture; achieved timing closure across SS, TT, and FF corners.
- Contributed to block-level floorplanning, including pin assignment, IP integration, and RDL planning for CPU and AI accelerator designs; coordinated with layout teams for custom layout integration and database delivery.
- Performed Static Timing Analysis (PrimeTime) and parasitic extraction (StarRC) for accurate sign-off; mitigated IR-drop, crosstalk, and reliability issues, supporting successful tape-out of advanced AI and data center processors.
- Optimized Clock Tree Synthesis (CTS) for minimal skew and latency while balancing power and timing margins.
- Implemented ECO flows for late-stage timing fixes, reducing turnaround time and maintaining sign-off quality across modes.

Design Automation Lab, Illinois Institute of Technology, Chicago, USA

Aug 2023 – Dec 2023

Research Assistant

- Completed 500+ hours of RTL-to-GDSII flow implementation for 14nm and 28nm TSMC nodes under Dr. Ken Choi using Design Compiler and ICC2.
- Developed a custom floorplan and PDN methodology that improved IR-drop resilience, minimized post-powerplan shorts, and enhanced design scalability across MMMC/RC corners.
- Designed and validated chip integration workflows for floorplan and power grid planning, ensuring functional and electrical robustness across multiple corners.

ChipEdge Technology, Bengaluru, India

Oct 2022 – Jul 2023

Physical Design Apprentice

- Executed end-to-end physical design flow: Logic Synthesis, Floorplan, Placement, CTS, Routing, and Optimization for 14nm, and 28nm TSMC nodes.
- Resolved setup/hold violations and achieved timing closure for designs up to ~550K standard cells and 80 macros.
- Delivered clean GDSII by resolving DRC, LVS, ANT, and LEC issues; automated ECO cycles using TCL and Shell scripting.
- Gained hands-on experience in I/O planning, bump assignment, and custom layout for advanced FinFET/CMOS nodes.

EDUCATION

Illinois Institute of Technology, Chicago, USA

Jan 2022 – Dec 2023

Master of Science in Electrical Engineering

GPA: 3.53/4.0

Relevant Courses: Introduction to VLSI, CAD Techniques for VLSI Design, High-Performance VLSI/IC Systems, Digital SoC Design, Computer Organization and Design, RF Integrated Circuit Design

Gandhi Institute for Technology, Bhubaneswar, India

Aug 2014 – Jul 2018

Bachelor of Technology in Electrical Engineering

GPA: 8.1/10

Department Rank 1 (5th–8th Semester)

PROJECTS

OpenSPARC T1 Block-Level RTL-to-GDSII Design

Feb 2023

- Implemented block-level RTL-to-GDSII design on 14nm and 28nm nodes, achieving 75% core-area utilization and performing density sweeps to analyze congestion and routability.
- Optimized design using cell insertion and sizing techniques to eliminate DRVs such as capacitance and transistor violations.